

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

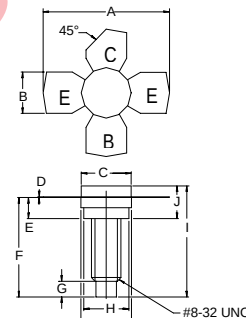
The **ASI BLX92A** is Designed for transmitting applications in class-A, B or C with a supply voltage up to 28 V

FEATURES:

- High Gain - 11.0 dB Min.
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	0.7 A
V_{CB}	65 V
P_{DISS}	6.0 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	-65 to +200 $^{\circ}\text{C}$
T_{STG}	-65 to +150 $^{\circ}\text{C}$
θ_{JC}	9.8 $^{\circ}\text{C/W}$

PACKAGE STYLE .280 4L STUD		
		
DIM	MINIMUM Inches / mm	MAXIMUM Inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10\text{ mA}$		65			V
BV_{CES}	$I_C = 10\text{ mA}$		65			V
BV_{CEO}	$I_C = 25\text{ mA}$		33			V
BV_{EBO}	$I_E = 1.0\text{ mA}$		4.0			V
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 100\text{ mA}$	10			---
f_T	$V_{CE} = 5.0\text{ V}$	$I_C = 100\text{ mA}$		1.2		GHz
C_c	$V_{CB} = 10\text{ V}$	$f = 1.0\text{ MHz}$		6.5		pF
C_e	$V_{EB} = 0\text{ V}$	$f = 1.0\text{ MHz}$		25		pF
P_G	$V_{CE} = 28\text{ V}$	$P_{OUT} = 2.5\text{ W}$	11			dB
η_C		$f = 470\text{ MHz}$	60			%